

**200mA 40V Low VF**

[Go to Home Page](#)

**Chip Information**

Chip Size	0.47 x 0.47mm
Pad Size	0.31 x 0.31mm
Chip Quantity	49966 pcs/wafer
Scribe Line Width	60um
Passivation	PSG
Wafer Size	5 inch
Top Metallization	Al(For Wire)

Chip Thickness/Back Metal : See below "Ordering Information"

**MAXIMUM RATINGS**

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	40	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR	25	V	
Average Forward Rectified Current	IF(AV)	200	mA	
Peak Forward Surge Current	IFSM	2	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

**ELECTRICAL CHARACTERISTICS**

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.500	0.480	0.440	V	IF=200mA Ta=25degC
	VF2	0.300	0.280	0.230	V	IF=10mA Ta=25degC
	VF3				V	
	VF4				V	
	VF5				V	
Maximum DC Reverse Current	IR1	70	50	15	uA	VR=25V Ta=25degC
	IR2				uA	
	IR3				uA	
	IR4				uA	
Reverse Breakdown Voltage	BV	40	44	55	V	IR=100uA
Junction Capacitance	Cj				pF	
Reverse Recovery Time	trr				nS	

**Ordering Information**

Chip Type	Chip Thickness	Back Metal
YHQ095	180 +/- 20um	Au(For Eutectic)
YHQ097	150 +/- 20um	Au(For Eutectic)
YHQ096	180 +/- 20um	Ti-Ni-Ag(For Ag Epoxy)

Note:  
Designed For RB495D